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Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

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1. Scope

The present specifications shall apply to Sanken silicon rectifier diode, AL01Z.

2. Outline

Туре	Silicon Rectifier Diode (Planar type)
Structure	Resin Molded
Applications	High Frequency Rectification, etc.

3. Flammability

UL94V-0 (equipment)

4. Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	V _{RSM}	V	200	
2	Peak Reverse Voltage	V _{RM}	V	200	
3	Average Forward Current	$I_{F(AV)}$	А	1.0	Refer to Derating of 7
4	Peak Surge Forward Current	I _{FSM}	А	25	10ms. Sine wave, one shot
5	Junction Temperature	T_j	°C	-40~+150	
6	Storage Temperature	T _{stg}	°C	-40~+150	

5. Electrical characteristics

No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	$V_{\rm F}$	V	0.98 max.	I _F = 1.0A
2	Reverse Leakage Current	I _R	μ A	50 max.	V _R =V _{RM}
3	Reverse Leakage Current Under High Temperature	HI _R	μ A	100 max.	V _R =V _{RM} , Tj=100°C
4	Reverse Recovery Time	trr-1	ns	50 max.	$I_F=I_{RP}=100$ mA, 90% Tj=25°C, Recovery point
4		trr-2	ns	35 max.	I_F =100mA, I_{RP} =200mA, Tj=25°C 75% Recovery point
5	Thermal Resistance	θ j-l	°C /W	22 max.	Between Junction and Lead





